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1	Probing the origins of magnetism in 2 at.% Fe-implanted 4H-SiC
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10	

#### 11 Abstract

Here we reported an about 2 at.% Fe-implanted p-type 4H-SiC Diluted Magnetic 12 Semiconductor (DMS). Scanning Transmission Electron Microscopy (STEM) and Atom 13 Probe Tomography (APT) techniques were used to investigate the origins of ferromagnetic 14 behavior. Nanoparticles (1-9 nm) were identified to be Fe<sub>3</sub>Si, Fe<sub>2</sub>Si, Fe<sub>5</sub>Si<sub>3</sub>, Fe<sub>3</sub>Si<sub>2</sub>, FeSi and 15 16 FeSi<sub>2</sub> phases, the distribution of which is related to Fe distribution. The magnetic properties were studied by Conversion Electron Mössbauer Spectroscopy (CEMS) and Superconducting 17 Quantum Interference Device (SQUID) techniques. The contributions of these Fe-silicides to 18 19 the ferromagnetism are thus discussed from a quantitative perspective.

20 Key words: DMS; APT; STEM; Fe implantation; ferromagnetism.

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In recent years, many efforts have been devoted to introduce 3d Transition Metals (TMs, 23 such as Cr, Mn, Co and Fe) in semiconductors in order to fabricate DMSs [1]. DMSs allow 24 manipulating the spin degree and the charge degree of the electrons separately and 25 26 simultaneously through the electrical and magnetic fields in one material. These DMSs should possess both considerable ferromagnetic properties at room temperature and relatively high 27 Curie temperature for industrial application. In practice, the realization of room-temperature 28 DMS is quite challenging. Although considerable explorations have been paid to some 29 semiconductors and oxides, like GaN-, Si-, GaAs-, ZnO- and TiO<sub>2</sub>- based [1-6], no room-30 temperature DMS has been successfully produced. 31

Much attention was also focused on some wide-bandgap semiconductors. SiC, with a wide bandgap (3.3 eV for 4H-SiC and 3.0 eV for 6H-SiC), high electrical breakdown field and high thermal conductivity, is used for high-temperature and high-power electronics [7]. Ab-initio calculations have predicted that doping SiC with TMs could result in a ferromagnetic ordering [8]. This phenomenon has been experimentally confirmed; ferromagnetic ordering appears at Curie Temperatures of 50, 250 and 270 K in Ni, Mn and Fe-implanted 6H-SiC [9]. High Curie Temperatures were also achieved in other TM-doped SiC semiconductors [10-14].

However, the origins of the magnetic effects were not clear. The magnetic components 39 40 could derive from defects [15, 16], defect-TM complexes [13, 17] or presence of secondphase particles [11, 18]. With the TM impurities beyond the solubility limit, spinodal 41 nanodecomposition as well as nanoprecipitation may occur in a range of semiconductor 42 43 compounds [3]. Among those, according to recent research, the second-phase particles could probably induce the ferromagnetism for Fe-doped SiC. In SiC matrix, the Fe reaction with 44 SiC at high temperature may induce the formation of binary Fe-silicides and ternary Fe-45 silicocarbides [10, 11, 13, 19, 20], some of which were reported to be magnetic. Due to the 46

presence of Fe<sub>3</sub>Si nanoparticles detected by APT in 6 at.% Fe-implanted 6H-SiC sample, a 67%
ferromagnetic component was obtained from CEMS spectra [11].

In order to achieve an in-depth understanding of the implantation induced magnetism, we tried to produce a 2 at.% Fe-implanted 4H-SiC DMS and performed careful analyses on the microstructure by advanced characterization techniques. The relationship between Fe distribution and its contribution on the magnetism was then explored from a quantitative view.

Commercial near (0001)-oriented p-type 4H-SiC substrates (provided by CREE, Durham, 53 NC, USA), with a 200 nm thickness uppermost epitaxial layer of p-type ( $n_A$ - $n_D \sim 10^{20}$  cm<sup>-3</sup>), 54 were co-implanted with 30-160 keV <sup>56</sup>Fe and <sup>57</sup>Fe ions. The integrated dose can reach 10<sup>16</sup> 55 ions/cm<sup>2</sup>, which induces a plateau of 2 at.% Fe concentration at a depth of 20-100 nm beneath 56 the sample surface according to the SRIM calculation [21] or experimental confirmation by 57 58 Rutherford backscattering spectroscopy [22, 23]. During ion implantation, the sample was held at 550 °C in order to avoid amorphization [22]. A rapid thermal annealing was then 59 performed at 1300 °C for 4 min to promote defect annihilation [24]. 60

The microstructure was examined by APT and (S)TEM. APT technique, based on field 61 evaporation [25], offers extensive capabilities for both 3D imaging and local chemical 62 analyses. Specimens for APT were prepared though the lift-out methods using a dual beam 63 SEM/FIB instrument (Zeiss Nvision 40). To conserve the region of interest (20-100 nm 64 beneath the surface), the Fe-implanted 4H-SiC sample was capped with 500-1000 nm of Pt. 65 Here, a Laser Assisted Wide Angle Tomographic Atom Probe (LAWATAP) was used to 66 perform the analysis, with a practical temperature of 80 K, a detection flux of 0.003-0.004 67 ions/s/cm<sup>2</sup> and a pulse repetition rate of 100 kHz. The wavelength of femtosecond laser pulse 68 is 343 nm. The GPM 3D software (From GPM lab, v. 6.4) was used to do the relevant data 69 reconstruction. The chemical compositions of the core nanoparticles were measured using the 70

- 3 -

iso-position cluster identification method [25]. (S)TEM was performed using a JEOL ARM200F instrument operated at 200 kV. Selected Area Electron Diffraction Patterns (SAEDPs)
and High Resolution TEM (HRTEM) images were taken to identify the crystal structures of
these nanoparticles. The structural information is collected from the Crystallography Open
Datasets and displayed by VESTA software [26].

76 <sup>57</sup>Fe CEMS technique was used at 300 K to analyze the near surface region of the irradiated sample since it has a penetration depth of about 80-100 nm [27, 28]. The spectra were 77 measured in normal incidence using a (He-5% CH<sub>4</sub>) gas flow proportional counter [29] and a 78 ~1.5 GBq radioactive source of <sup>57</sup>Co in Rh matrix in constant acceleration mode. The CEMS 79 spectra were fitted by using the four components of the Gunnlaugsson model [30] and a Fs 80 (ferro) component. The single Fe<sub>i</sub> (C) and Fe<sub>i</sub> (Si) lines are attributed to the interstitial sites of 81 Fe atoms surrounded by four C or Si atoms, respectively. The Fs (para) component 82 corresponds to the positioning of the substitutional Fe atoms in C or Si sites. The Fd fraction 83 is assigned to Fe atoms located in strongly disturbed zones. Besides the four components, the 84 Fs (ferro) component was used for the Fe atoms contained in the nanoparticles and the Fe 85 atoms diluted in the matrix for the ferromagnetic contribution. By differentiating 86 quantitatively paramagnetism and ferromagnetism, <sup>57</sup>Fe CEMS is very useful for interpreting 87 the magnetization data measured by a MPMS 5XL SQUID magnetometer at 300 K and 10 K. 88

Here, STEM and APT were used to investigate the microstructure, and fine magnetic characterizations were performed by CEMS and SQUID. The magnetic nanoparticles were then correlated to the magnetism.

92 Fig. 1(a)-(c) exhibit massive nanoparticles from 3 different APT samples.

93

Fig. 1

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These observed particles have a diameter of 1-8 nm. The calculated Fe/Si ratio for those 94 with a minimum number of 60 atoms in core particle was plotted in Fig. 1(d). These 95 nanoparticles correspond to a chain of Fe-silicides, including Fe<sub>2</sub>Si, Fe<sub>5</sub>Si<sub>3</sub>, Fe<sub>3</sub>Si<sub>2</sub>, FeSi and 96 97 FeSi<sub>2</sub>, among which some with a higher Fe/Si ratio (or higher Fe concentration) may grow to a larger size. Notably, some C atoms were also observed in the core of particles, as exhibited 98 in Fig. 1(e). In fact, the Fe, Si and C concentration values in these nanoparticles depend on the 99 atomic or molecular trajectory and the subsequent 3D reconstruction. SiC has a higher 100 101 evaporation field than nanoparticles, which may lead to a trajectory aberration due to the local magnification effect [25]. Other phenomena, including the molecular ion evaporation [31] and 102 103 the multiple events [31, 32] may also blur the C projection trajectory, making its identification more complex in SiC. It remains a question that whether these nanoparticles behave as 104 nanoclusters containing C atoms or nanoparticles without C atoms inside. 105

The crystal structures of nanoparticles were thus explored by (S)TEM analyses. From the 106 107 HRTEM image in Fig. 2(a), one particle embedded in matrix can be distinguished. This nanoparticle exhibits lattice coherency with matrix. As seen in the Fast Fourier Transform 108 (FFT) images of the nanoparticle (in Fig. 2(b)) and matrix (in Fig. 2(c)), there is a small 109 110 lattice misfit along the horizontal direction. This is also clear in the local magnification map in Fig. 2(d). 4H-SiC phase (space group: P 63 m c) possesses hexagonal close-packed 111 symmetry, in which "4" refers to the atomic layers in a repeat unit along the stacking direction 112 and H represents the crystal symmetry. The interplanar distances of {0116} and {1000} 113 planes are 0.142 nm and 0.267 nm, respectively. In the nanoparticle, the cubic Fe<sub>3</sub>Si phase 114 (space group: F m  $\overline{3}$  m) is evidenced by two vertical lattice parameters, 0.140 nm and 0.250 115 nm, corresponding to the inter-planar distances of {400} and {021} planes, respectively. It is 116 inferred that the {400} plane of Fe<sub>3</sub>Si phase is oriented with {0116} plane of 4H-SiC matrix. 117

Fig. 2

The hexagonal Fe<sub>2</sub>Si phase (space group:  $P\overline{3}$  m 1) could be identified from Fig. 2(e) and (f), 119 which reveal the SAEDPs along two distinct orientations (not the exact zone axes). The 120 extracted lattice parameters, with the values in the range 0.2018-0.2028 nm, correspond to the 121 theoretical lattice parameter of {2110} planes (with a value of 0.2026 nm) of Fe<sub>2</sub>Si phase. The 122 123 SAEDPs for the nanoparticles can only be recorded from some fields of view aligned with specific orientations, requiring tentative rotation operations. In Fig. 2(g), some ring traces 124 125 were observed from the SAEDP image and the corresponding interplanar distances were measured. After comparison with all the possible lattice parameters among all Fe-silicides, 126 Fe<sub>5</sub>Si<sub>3</sub> phase (space group: P 6<sub>3</sub> m c m) could be unambiguously identified. 127

Thus, the presence of several Fe-silicides was confirmed. The repeated lattice cells for cubic Fe<sub>3</sub>Si phase, hexagonal Fe<sub>2</sub>Si phase and hexagonal Fe<sub>5</sub>Si<sub>3</sub> phase are plotted in Fig. 2(h)-(j). Since these Fe-silicides exhibit their predicted crystal structures, it is very unlikely that a significant proportion of C atoms are present in these particles. It is hence inferred that the detected C atoms in the nanoparticles should come from APT artefacts.

133 These nanoparticles formed during thermal annealing display simultaneously a size and a composition gradient along implantation depth. In Fig. 3(a), the phase of these nanoparticles 134 evolves from Fe-rich type (Fe<sub>2</sub>Si) to Si-rich type (FeSi<sub>2</sub>) within an implantation depth 20-100 135 136 nm, along with the size decrease. These observations are consistent with the Fe distribution. Based on the calculation shown in Fig. 3(b), Fe concentration peaks at a penetration depth of 137 20-45 nm, corresponding to the presence of most Fe<sub>2</sub>Si-type nanoparticles. Due to limited 138 139 reconstruction volume in APT, no Fe<sub>3</sub>Si-type nanoparticle was observed in this sample. TEM photograph in Fig. 3(c) reveals a 1-9 nm size-gradient distribution of nanoparticles beneath 140 the implantation surface, which perfectly agrees with APT analyses. These nanoparticles 141

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show various shapes (regular and irregular). This may partly explain why the Chemical
Composition Correction (CCC) model [33] fails to correct the particle composition, since this
model is adapted to cubic or spherical nanoparticles.

145

#### *Fig. 3*

At high temperature, a variety of stable and metastable phases appear in the binary Fe-Si phase diagram [34]. A stronger Fe-Si affinity promotes the preferential formation of Fesilicides rather than carbides. The formation of Fe<sub>3</sub>Si could be ascribed to its high standard formation enthalpy of -94.1 kJ/mol [35], in comparison to that of 25.2 kJ/mol for Fe<sub>3</sub>C [35].

Here, the possibility that ternary Fe-silicocarbides (including  $Fe_{65}Si_{25}C_{10}$ ,  $Fe_{70}Si_{10}C_{20}$ , Fe<sub>70</sub>Si<sub>15</sub>C<sub>15</sub>, reported in [20]) are formed could be excluded, because these compounds are in an amorphous condition at above 1000 °C. For instance,  $Fe_{65}Si_{25}C_{10}$  will decompose above 737 K [20].

Moreover, the Fe concentration at the SiC interface determines the types of the Fe-silicides. 154 Fe concentration decreases monotonously within the implantation depth 20-100 nm. The Fe 155 diffusion is motivated by the vacancies produced during ion implantation. The high vacancy 156 concentration near the surface region results in a corresponding high Fe concentration, since 157 158 the vacancies prefer to stay closer to the free surface [36]. As measured from Fig. 3(b), the average Fe concentration is  $2.5 \pm 0.2$  at.% at a depth range 16-45 nm, and thus Fe<sub>2</sub>Si-type 159 160 nanoparticles were formed. In accordance with the decreasing Fe concentration, a chain of Fesilicides were observed. 161

Fig. 4(a) plots the CEMS spectra obtained at ambient temperature for the as-annealed sample. The spectra were fitted with 2 paramagnetic components (Fe<sub>i</sub> (C) and Fs (para)) of the Gunnlaugsson model and one ferromagnetic component (Fs (ferro)). Another 2 components, Fe<sub>i</sub> (Si) and Fd, were neglected since the samples were annealed at 1300°C [35]. The analyses

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reveal that Fe atoms distribute in different environments. The ferromagnetic spectrum 166 originates from the ferromagnetic ordering of Fe. The hyperfine field distribution in Fig. 4(b) 167 reveals an about 32% contribution of ferromagnetic component. The ordered Fe<sub>3</sub>Si phase was 168 169 frequently reported in the literature because of its ferromagnetic contribution [11, 37-39]. The low intensity at two intensity peaks (typically 20T and 30T [11]) suggests a low volume 170 fraction of ordered Fe<sub>3</sub>Si phase. This well agrees with the fact that a few Fe<sub>3</sub>Si-type 171 nanoparticles were observed from APT and TEM analyses. Indeed, the Fs (ferro) component 172 could be due to other types of Fe-silicides and Fe atoms diluted in the matrix. With half-173 metallic band structure, hexagonal Fe<sub>2</sub>Si phase is ferromagnetic and the magnetic moment is 174 175 about 1.30 µB/Fe [40-42]. For ferromagnetic Fe<sub>5</sub>Si<sub>3</sub> phase, it has two unequal sites, with magnetic moments of 1.05 µB/Fe and 1.55 µB/Fe [40], respectively. Thus, the average 176 magnetic moment of Fe<sub>5</sub>Si<sub>3</sub> is 1.30 µB/Fe. The magnetic moment values for other Fe-silicides 177 178 can be referred to the literature [40, 41, 43].

179

#### Fig. 4

Fig. 4(c)-(d) show the M-H curves at 10 K and 300 K. In Fig. 4(c), the hysteretic behavior is clear at low fields and the saturation magnetization is about 1.40  $\mu$ B/Fe at 10 K. In contrast, no hysteretic behavior was observed in Fig. 4(d) at low fields at 300 K. This demonstrates the ferromagnetic behavior at 10 K and the superparamagnetic behavior at 300 K.

Then, we discuss the ferromagnetism at 10 K. 4H-SiC matrix is diamagnetic and the implanted Fe atoms induce the ferromagnetic behavior. The ferromagnetism is an accumulation of total Fe atoms, as expressed below:

187 
$$\langle M \rangle = \sum_{i=1}^{n} f_i \langle M \rangle_i$$

188 where  $\langle M \rangle$  is the saturation magnetization, about 1.40 µB/Fe at 10 K,  $f_i$  and  $\langle M \rangle_i$  are the Fe 189 fraction and the magnetic moment in each component. Taking into account the presence of Fe-rich nanoparticles, Fe in 4H-SiC matrix contains two parts: Fe atoms in matrix and insideFe-silicides. Thus, the above equation can be written as:

192 
$$\langle M \rangle = f_{diluted} \langle M \rangle_{diluted} + f_{nano} \langle M \rangle_{nano}$$

where  $\langle M \rangle_{diluted}$  and  $\langle M \rangle_{nano}$  represent the average magnetic moments for the Fe atoms in matrix and inside nanoparticles, respectively, and  $f_{diluted}$  and  $f_{nano}$  are the Fe fractions in matrix and inside nanoparticles. The Fe distribution is extracted from APT analyses and the results are listed in Table 1.

197

Table 1Fe distribution and the magnetic contributions

		Nanoparticles				
	Matrix _	Fe <sub>2</sub> Si	Fe5Si3	Fe <sub>3</sub> Si <sub>2</sub>	FeSi	FeSi <sub>2</sub>
<i>f</i> <sub>i</sub> / %	48.3	34.6	6.1	8.0	2.6	0.4
〈 <i>M<sub>i</sub></i> 〉/ μB/Fe	1.59	1.3 [40-42]	1.3 [40]	0.79 [43]	0.75 [43]	0 [43]
〈M〉 <sub>nano</sub> / μB/Fe		1.18				

## 198 Note: $\langle M \rangle_{\text{nano}}$ represents the average magnetic moment for the Fe atoms inside nanoparticles.

199 From APT analyses, about 51.7% of total Fe atoms form Fe-silicides. The average magnetic moment of nanoparticles is about 1.18 µB/Fe, while that for diluted Fe atoms is about 1.59 200 201 µB/Fe. The magnetic moment for the diluted Fe atoms is close to that for 6 at.% Fe implanted 6H-SiC, with a value of 1.65 µB/Fe [44]. Fe<sub>2</sub>Si phase, with a Fe fraction of 34.6%, is the main 202 contributor among all the Fe-silicides. The half-metallic ferromagnetism of Fe<sub>2</sub>Si is mainly 203 due to the Fe *d*-*d* exchange as well as the hybridization between Si *p* and Fe *d* orbitals [45]. 204 Compared with 6 at.% Fe, a 2 at.% Fe implantation induces a larger variety of Fe-silicides, 205 206 while, in both cases, not only the diluted Fe atoms but the Fe atoms inside nanoparticles are also important to the ferromagnetism. According to *ab initio* calculations, the ferromagnetic 207 ordering within the diluted Fe atoms derives from the Si substitution by Fe in the (Si/4C) 208

tetrahedron, in which the electronic structure of Fe atoms is strongly affected by the neighboring C atoms [46]. An increase of the Fe-C length along the *c* direction of this (Fe/4C) tetrahedron leads to the increased mean magnetic moment [46]. Calculated densities of states on Si substitution with Fe reveal the Fe bands in the gap close to the SiC valence band top, in which a significant degree of coupling exists between Fe 3*d* and C 2*p* orbitals [46, 47].

To conclude, this work concentrates on a 2 at.% Fe-implanted 4H-SiC DMS. Combined 214 high resolution APT and STEM analyses reveal a chain of magnetic Fe-silicides, including 215 Fe<sub>3</sub>Si, Fe<sub>2</sub>Si, Fe<sub>5</sub>Si<sub>3</sub>, Fe<sub>3</sub>Si<sub>2</sub>, FeSi and FeSi<sub>2</sub>, which display both size and composition gradient 216 characteristics along the implantation depth. Fe<sub>2</sub>Si phase possesses larger proportion than any 217 other type. The DMS exhibits a ferromagnetic behavior at 10 K and the ferromagnetism 218 219 originates from both the diluted Fe atoms and Fe-silicides. The average magnetic moment of 220 nanoparticles was estimated to be about 1.18 µB/Fe, while that for diluted Fe atoms is about 1.59 µB/Fe at 10 K. 221

## 222 Declaration of Competing Interest

The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

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## **Graphical abstract**





Fig. 1 Distribution map of Fe atoms and nanoparticles in 2 at.% Fe-implanted 4H-SiC after annealing at 1300 °C for 4 min: (a)-(c) three reconstructed APT tips with the identified nanoparticles; (d) the calculated Fe/Si ratio from the core nanoparticles (for those with 60 atoms in minimum); (e) the calculated atomic concentrations of the core nanoparticles (for those with 60 atoms in minimum). In (d), the dashed lines correspond to different types of Fe-silicides.



Fig. 2 STEM/HRTEM analyses of crystal structures for  $Fe_3Si$ ,  $Fe_2Si$  and  $Fe_5Si_3$  phases: (a) HRTEM image revealing cubic  $Fe_3Si$  phase; (b)-(c) the FFT images of the nanoparticle (as marked with "1") and the matrix (as marked with "2"); (d) the local magnification image displaying the matrix-nanoparticle interface (as marked with "3"); (e)-(f) the SAEDP images showing hexagonal  $Fe_2Si$  phase; (g) the SAEDP image (as well as the inserted one with distinct contrast) with the corresponding interplanar distances revealing the hexagonal  $Fe_5Si_3$  phase; (h)-(j) the repeated lattice cells of  $Fe_3Si$ ,  $Fe_2Si$  and  $Fe_5Si_3$  phases from VESTA software, respectively.



Fig. 3 Distribution map of the nanoparticles from APT and TEM analyses: (a) reconstructed APT tip revealing the gradient distribution of a chain of Fe-silicides (including  $Fe_2Si$ ,  $Fe_5Si_3$ ,  $Fe_3Si_2$ , FeSi and  $FeSi_2$ ); (b) Fe distribution along the irradiation depth; (c) the nanoparticles formed beneath the implantation surface.



Fig. 4 Photographs exhibiting the room-temperature CEMS spectra (a) with the corresponding hyperfine field distribution (b) and the magnetization hysteresis curves measured at 10 K (c) & 300 K (d) for the samples annealed at 1300 °C for 4 min. In (a), the whole spectrum (in blue) and 3 components consisting of the  $Fe_i$  (C) component (in green), the Fs (para) component (in orange) and the Fs (ferro) component (in purple) are displayed. In (c) & (d), the inserted photos show the magnetization behaviors at low fields.

